

Schottky barrier diode

RB706F-40 / RB706D-40

●Applications

General purpose detection
High speed switching

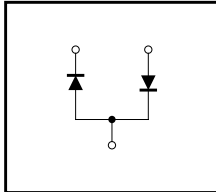
●Features

- 1) Small surface mounting dual element linear type.
(SMD3, UMD3)
- 2) Low V_F and low I_R .
- 3) High reliability.

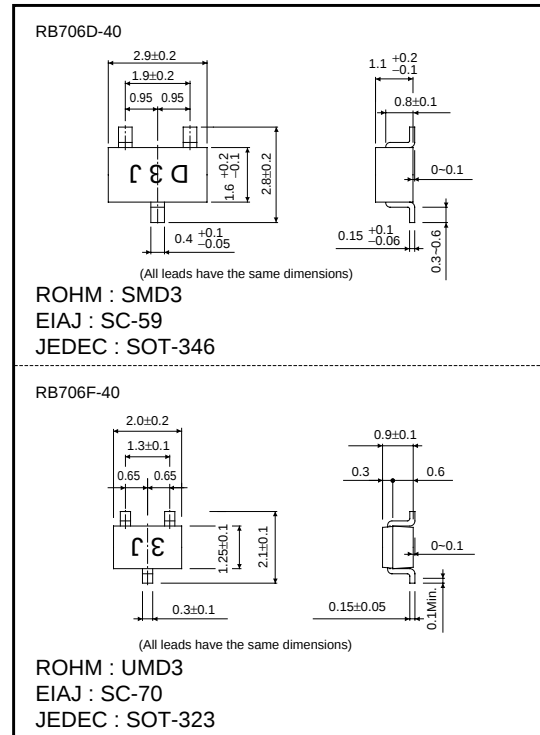
●Construction

Silicon epitaxial planar

●Circuit



●External dimensions (Units : mm)



●Absolute maximum ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	45	V
DC reverse voltage	V_R	40	V
Mean rectifying current	I_O	30	mA
Peak forward surge current *	I_{FSM}	200	mA
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-40~+125	$^\circ\text{C}$

*60 Hz for 1

Diodes

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V _F	–	–	0.37	V	I _F =1mA
Reverse current	I _R	–	–	1	μA	V _R =10V
Capacitance between terminals	C _T	–	2.0	–	pF	V _R =1V, f=1MHz

Note) ESD sensitive product handling required.

●Electrical characteristic curves (Ta = 25°C)

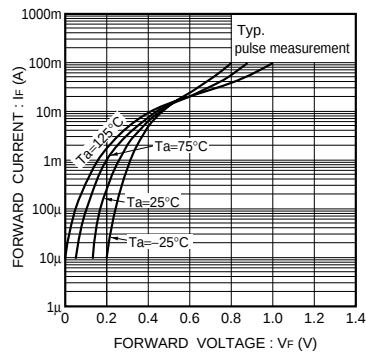


Fig. 1 Forward characteristics

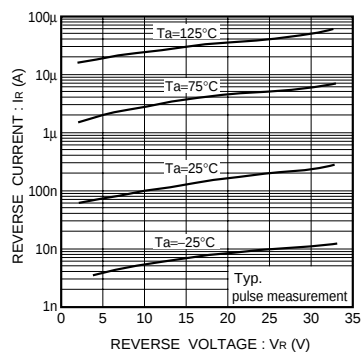


Fig. 2 Reverse characteristics

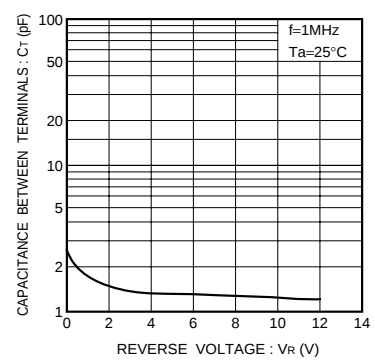
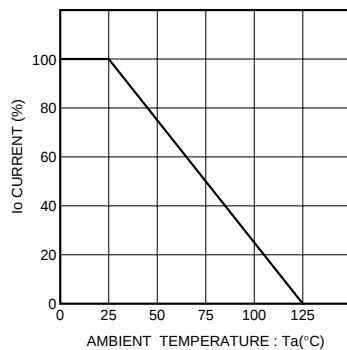


Fig. 3 Capacitance between terminals characteristics

Fig. 4. Derating curve
(mounting on glass epoxy PCBs)